

RJK4513DPE

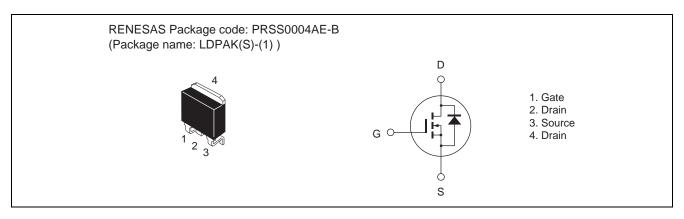
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1586-0100 Rev.1.00 Dec 08, 2009

Features

- Low on-resistance $R_{DS(on)}=0.33~\Omega~typ.~(at~I_D=8~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	450	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I _D	16	А
Drain peak current	I _{D (pulse)} Note1	48	А
Body-drain diode reverse drain current	I _{DR}	16	А
Body-drain diode reverse drain peak current	I _{DR} (pulse)	48	А
Avalanche current	I _{AP} Note3	4	А
Avalanche energy	E _{AR} Note3	0.9	mJ
Channel dissipation	Pch Note2	100	W
Channel to case thermal impedance	θch-c	1.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

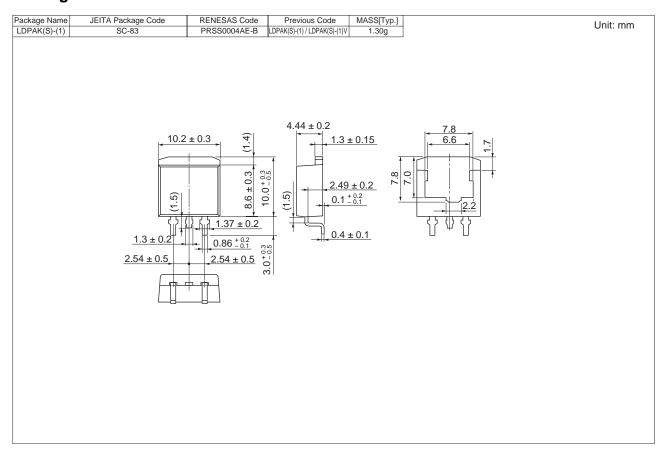
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 450 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.33	0.38	Ω	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1450	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	162	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	18	_	pF	
Turn-on delay time	t _{d(on)}	_	33	_	ns	I _D = 8A
Rise time	t _r	_	28	_	ns	$V_{GS} = 10 \text{ V}$ $R_L = 28.1 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	84	_	ns	
Fall time	t _f	_	17	_	ns	
Total gate charge	Qg	_	37.1	_	nC	V _{DD} = 360 V
Gate to source charge	Qgs	_	7.5	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	16.9	_	nC	I _D = 16 A
Body-drain diode forward voltage	V_{DF}	_	0.89	1.50	V	$I_F = 16 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	290	_	ns	$I_F = 16 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK4513DPE-00-J3	1000 pcs	Taping

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